



B5817W-B5819W

Schottky Barrier Diode



Features

- ❖ For use in low voltage, high frequency inverters
 - ❖ Free wheeling, and polarity protection applications.

Marking : B5817W: SJ

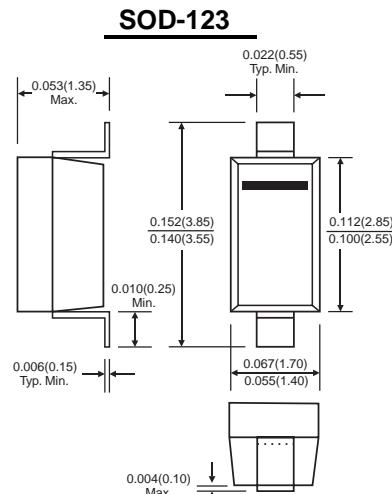
B5818W:SK

B5819W: SL

Maximum Ratings and Electrical Characteristics

Rating at 25°C ambient temperature unless otherwise specified.

Dimensions in inches and (millimeters)



Maximum Ratings and Electrical Characteristics

Parameter	Symbol	B5817W	B5818W	B5819W	Unit
Non-Repetitive Peak reverse voltage	V _{RM}	20	30	40	V
Peak repetitive Peak reverse voltage	V _{RRM}				
Working Peak Reverse Voltage	V _{RWM}	20	30	40	V
DC Blocking Voltage	V _R				
RMS Reverse Voltage	V _{R(RMS)}	14	21	28	V
Average Rectified Output Current	I _O		1		A
Peak forward surge current @=8.3ms	I _{FSM}		25		A
Repetitive Peak Forward Current	I _{FRM}		625		mA
Power Dissipation	P _d		250		mW
Thermal Resistance Junction to Ambient	R _{θJA}		500		K/W
Storage temperature	T _{STG}		-65~+150		°C

ELECTRICAL CHARACTERISTICS

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Reverse breakdown voltage	$V_{(BR)}$	$I_R = 1\text{mA}$ B5817W B5818W B5819W	20 30 40		V
Reverse voltage leakage current	I_R	$V_R=20\text{V}$ B5817W $V_R=30\text{V}$ B5818W $V_R=40\text{V}$ B5819W		1	mA
Forward voltage	V_F	B5817W	$I_F=1\text{A}$	0.45	V
			$I_F=3\text{A}$	0.75	
		B5818W	$I_F=1\text{A}$	0.55	V
			$I_F=3\text{A}$	0.875	
Diode capacitance	C_D	B5819W	$I_F=1\text{A}$	0.6	V
			$I_F=3\text{A}$	0.9	
Diode capacitance	C_D	$V_R=4\text{V}, f=1\text{MHz}$		120	pF

Typical Characteristics

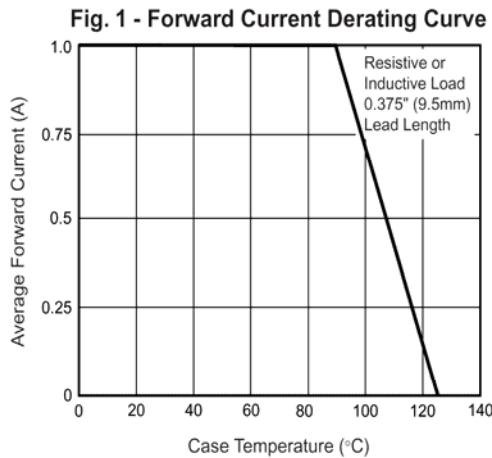


Fig. 2 - Maximum Non-Repetitive Peak Forward Surge Current

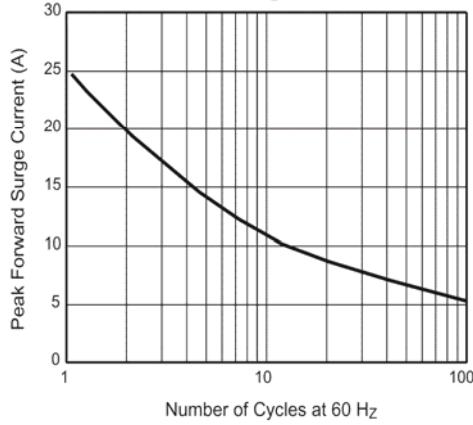


Fig. 3 - Typical Instantaneous Forward Characteristics

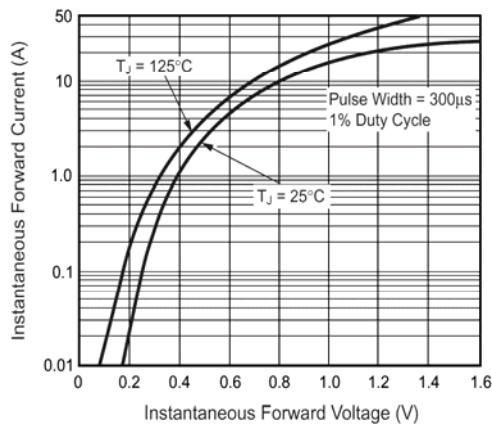


Fig. 4 - Typical Reverse Characteristics

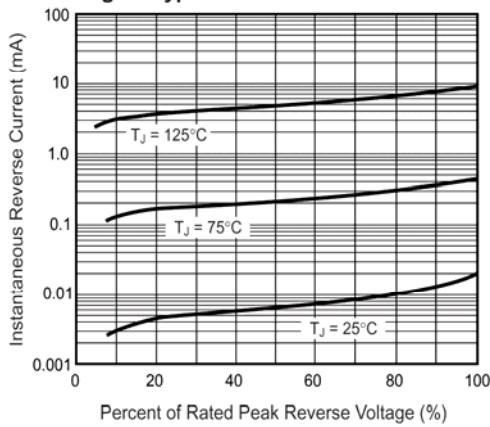


Fig. 5 - Typical Junction Capacitance

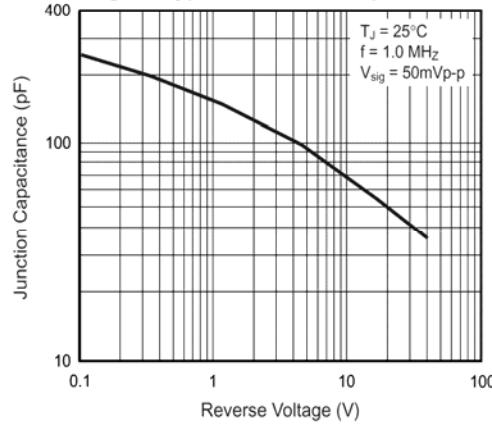


Fig. 6 - Typical Transient Thermal Impedance

